CHAPTER 18:
ELECTRICAL PROPERTIES

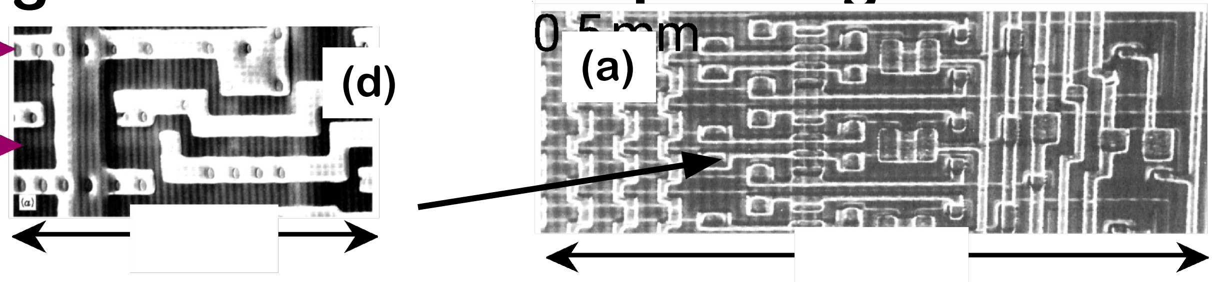
ISSUES TO ADDRESS...

- How are electrical conductance and resistance characterized?
- What are the physical phenomena that distinguish conductors, semiconductors, and insulators?
- For metals, how is conductivity affected by imperfections, T, and deformation?
- For semiconductors, how is conductivity affected by impurities (doping) and T?

VIEW OF AN INTEGRATED CIRCUIT

- Scanning electron microscope images of an IC:

45 μm



- A dot map showing location of Si (a semiconductor):
  --Si shows up as light regions.

- A dot map showing location of Al (a conductor):
  --Al shows up as light regions.

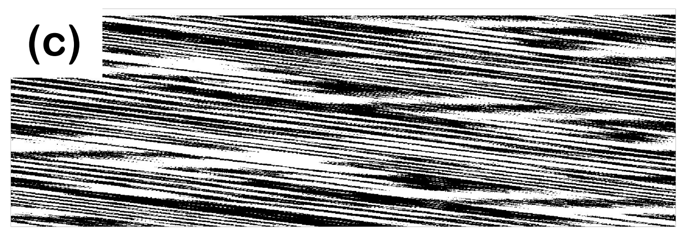


Fig. (d) from Fig. 18.25, *Callister 6e*. (Fig. 18.25 is courtesy Nick Gonzales, National Semiconductor Corp., West Jordan, UT.)

Fig. (a), (b), (c) from Fig. 18.0, *Callister 6e*.

ELECTRICAL CONDUCTION

- **Ohm's Law:**

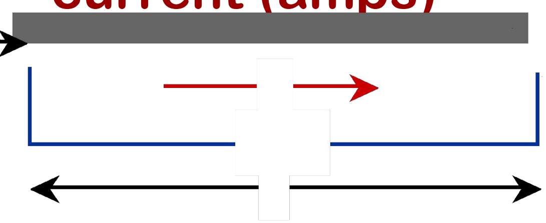
$$\Delta V = I R$$

voltage drop (volts)

current (amps)

resistance (Ohms)

A (cross sect. area)



- **Resistivity, ρ and Conductivity, σ:**
  --geometry-independent forms of Ohm's Law

$$\frac{DV}{L} = \frac{I}{A} r$$

E: electric field intensity

resistivity (Ohm-m)

J: current density

conductivity

$$s = \frac{l}{r}$$

- **Resistance:**

$$R = \frac{r L}{A} = \frac{L}{A s}$$

CONDUCTIVITY: COMPARISON

• **Room T values (Ohm-m)$^{-1}$**

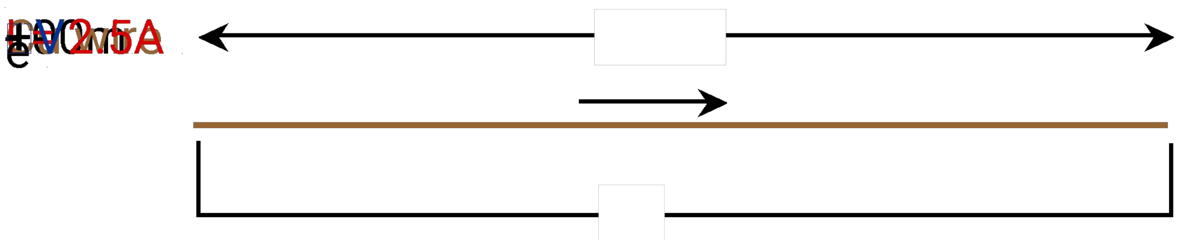
Aluminum oxide $<10^{-13}$

Selected values from Tables 18.1, 18.2, and 18.3, *Callister 6e*.

EX: CONDUCTIVITY PROBLEM

- Question 18.2, p. 649, *Callister*

6e:



What is the minimum diameter (D) of the wire so that

$\Delta V < 1.5V$?

$$R = \frac{L}{A s} = \frac{DV}{I}$$

100m → L

< 1.5V → DV

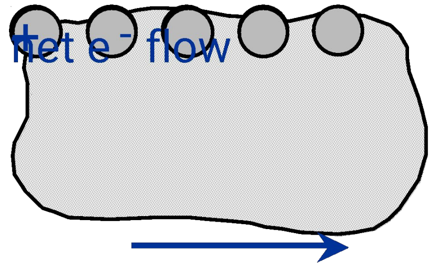
2.5A → I

$\frac{pD^2}{4}$ → A

6.07×10^7 (Ohm-m)$^{-1}$ → s

Solve to get **D > 1.88 mm**

CONDUCTION & ELECTRON TRANSPORT



- **Metals:**

-- Thermal energy puts many electrons into a higher energy state.

- **Energy States:**

-- the cases below for metals show that nearby energy states are accessible by thermal fluctuations.

ENERGY STATES: INSULATORS AND SEMICONDUCTORS

- **Insulators:**

  --Higher energy states not

- **Semiconductors:**

  --Higher energy states separated by a smaller gap

METALS: RESISTIVITY VS T, IMPURITIES

- Imperfections increase resistivity
  - --grain boundaries
  - --dislocations
  - --impurity atoms

These act to scatter electrons so that they take a less direct path.

- Resistivity increases with:
  - --temperature
  - --wt% impurity
  - --%CW

$$r = r_{thermal}$$

$$+ r_{thermal}$$

$$+ r_{def}$$

Adapted from Fig. 18.8, *Callister 6e.* (Fig. 18.8 adapted from J.O. Linde, *Ann. Physik* 5, p. 219 (1932); and C.A. Wert and R.M. Thomson, *Physics of Solids*, 2nd ed., McGraw-Hill Book Company, New York, 1970.)

EX: ESTIMATING CONDUCTIVITY

- Question: Estimate the electrical conductivity of a Cu-Ni

Adapted from Fig. 7.14(b), *Callister 6e.*

$$r = 30\mathrm{x}10^{-8}\ \mathrm{Ohm - m}$$

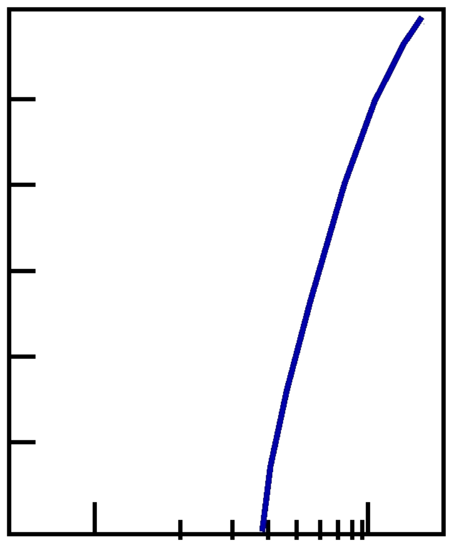
$$s = \frac{1}{r} = 3.3\mathrm{x}10^{6}\ (\mathrm{Ohm - m})^{-1}$$

Adapted from Fig. 18.9, *Callister 6e.*

PURE SEMICONDUCTORS: CONDUCTIVITY VS T

- Data for **Pure Silicon**:
  - --σ increases with T
  - --opposite to metals

$$\sigma_{undoped} \propto e^{-E_{gap}/kT}$$



electrons can cross gap at higher T

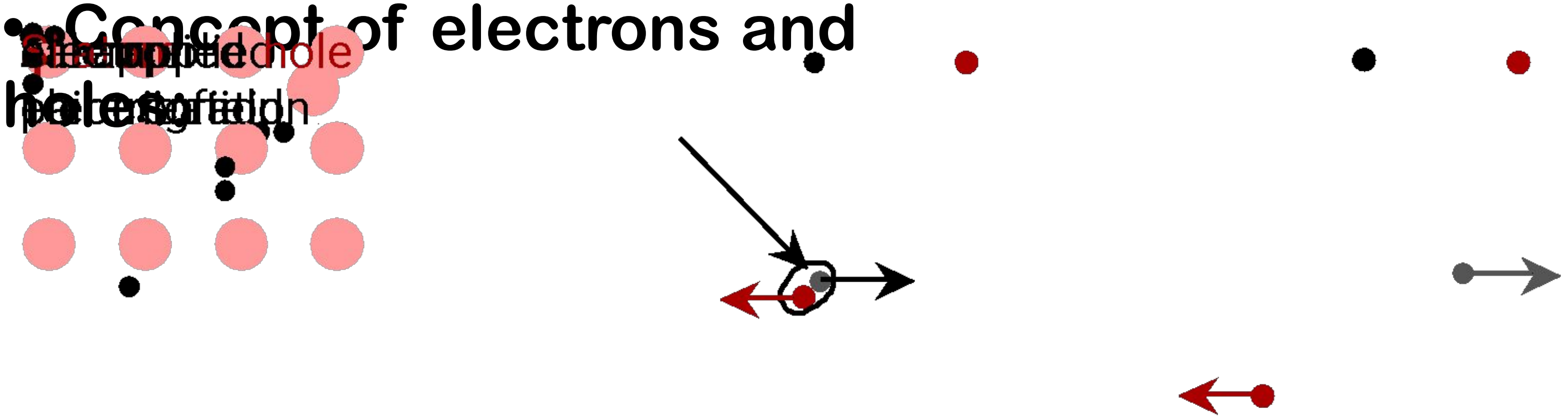
material	band gap (eV)
Si	1.11
Ge	0.67
GaP	2.25
CdS	2.40

Selected values from Table 18.2, *Callister 6e.*

Adapted from Fig. 19.15, *Callister 5e.* (Fig. 19.15 adapted from G.L. Pearson and J. Bardeen, *Phys. Rev.* 75, p. 865, 1949.)

CONDUCTION IN TERMS OF ELECTRON AND HOLE MIGRATION

- Concept of electrons and holes:



- Electrical Conductivity given by:

$$\sigma = n|e|\mu_e + p|e|\mu_h$$

holes/m^3

hole mobility

electrons/m^3

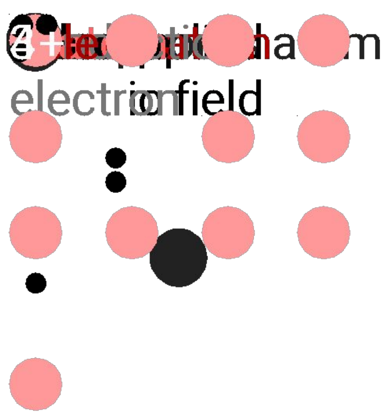
electron mobility

Adapted from Fig. 18.10, *Callister 6e.*

INTRINSIC VS EXTRINSIC CONDUCTION

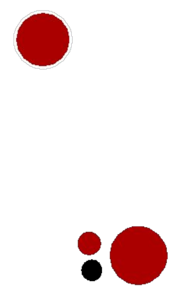
- **Intrinsic**:
  # electrons = # holes (n = p)
  --case for pure Si
- **Extrinsic**:
  --n $\neq$ p
  --occurs when impurities are added with a different
  # valence electrons than the host (e.g., Si atoms)

- **N-type** Extrinsic: (n >> p)



s ª $n|e|m_e$

- **P-type** Extrinsic: (p >> n)



s ª $p|e|m_h$

DOPED SEMICON: CONDUCTIVITY VS T

- Data for Doped Silicon:
  --σ increases doping
  --reason: imperfection sites lower the activation energy to produce mobile electrons.

- Comparison: intrinsic vs extrinsic conduction...
  --extrinsic doping level: $10^{21}/m^3$ of a n-type donor impurity (such as P).
  --for T < 100K: "freeze-out" thermal energy insufficient to excite electrons.
  --for 150K < T < 450K: "extrinsic"
  --for T >> 450K: "intrinsic"

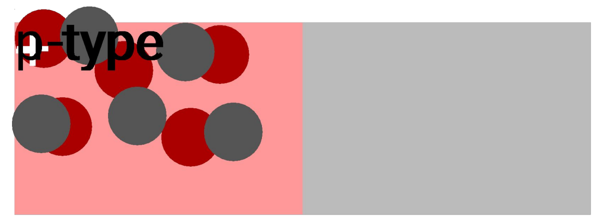
Adapted from Fig. 18.16, *Callister 6e*. (Fig. 18.16 from S.M. Sze, *Semiconductor Devices, Physics, and Technology*, Bell Telephone Laboratories, Inc., 1985.)

Adapted from Fig. 19.15, *Callister 5e*. (Fig. 19.15 adapted from G.L. Pearson and J. Bardeen, *Phys. Rev.* 75, p. 865, 1949.)

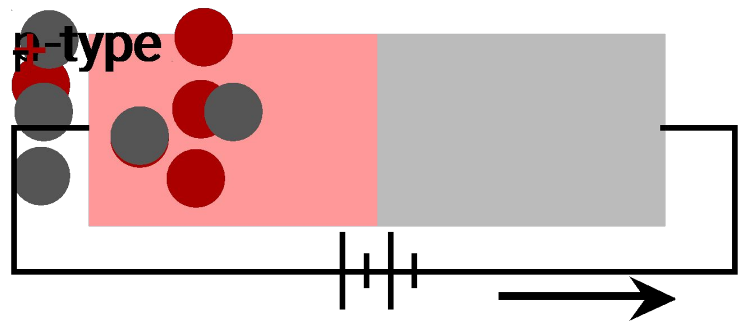
P-N RECTIFYING JUNCTION

- Allows flow of electrons in one direction only (e.g., useful to convert alternating current to direct current.
- Processing: diffuse P into one side of a B-doped crystal.
- Results:

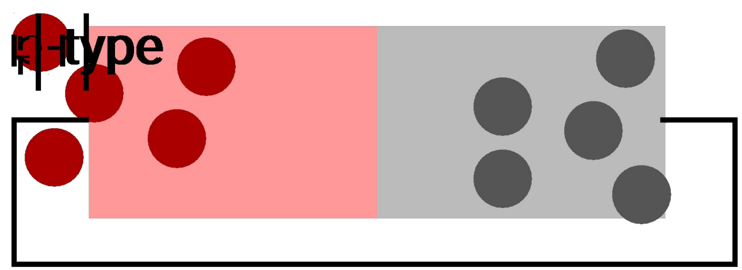
--No applied potential:
no net current flow.



--Forward bias: carrier
flow through p-type and
n-type regions; holes and
electrons recombine at
p-n junction; current
flows.



--Reverse bias: carrier
flow away from p-n junction;
carrier conc. greatly
reduced
at junction; little current
flow.



SUMMARY

- Electrical conductivity and resistivity are:
  --material parameters.
  --geometry independent.
- Electrical resistance is:
  --a geometry and material dependent parameter.
- Conductors, semiconductors, and insulators...
  --different in whether there are accessible energy
  states for conductance electrons.
- For metals, conductivity is increased by
  --reducing deformation
  --reducing imperfections
  --decreasing temperature.
- For pure semiconductors, conductivity is increased by
  --increasing temperature
  --doping (e.g., adding B to Si (p-type) or P to Si (n-type).

ANNOUNCEMENTS

Reading:

Core
Problems:

Self-help
Problems: